

REMARKS

Claims 1, 2 and 4-23 remain present in this application.

Claims 1 stands rejected under 35 USC 102(e) as being anticipated by Tran, U.S. Patent 6,844,591. This rejection is respectfully traversed.

It is respectfully submitted that the method of independent claim 1 differs from Tran, as the trench of a transistor of Tran is irrelevant to the trench isolation structure of the present application. Referring to Figs. 7 and 9 and column 5, lines 17-21 of Tran, the trench 30 indicated by the Examiner is directed to a transistor having a gate oxide 32, a polysilicon gate layer 35, and a conductive layer 40 formed therein. However, claim 1 of the present application recites a method of forming a trench isolation structure having a polysilicon liner for enhancing the adhesion between trench sidewalls and a spin-on-glass in order to prevent cracks from forming due to poor adhesion between the trench sidewall surfaces and the spin-on-glass. The polysilicon liner of independent claim 1 is not a gate layer as taught by Tran. The gate layer taught by Tran does not exhibit the advantages of the polysilicon liner of independent claim 1.

Claim 18 stands rejected under 35 USC 102(e) as being anticipated by Ranade et al., U.S. Publication 2004/0180510. This rejection is respectfully traversed.

As discussed in the Amendment filed on December 12, 2005, the step of baking in the present application is different from the thermal process disclosed in Ranade et al. The thermal process of Ranade et al is for forming the oxide layer (see paragraph [0037]) but the backing step of the present invention is not. Specifically, the oxide layer of the present invention is formed during the annealing step after the CMP step, rather than in this baking step (see paragraph [0014] and Fig. 4). In other words, the baking step is conducted before the annealing step and

the CMP step. The purpose of the baking process is not to form the dielectric layer in present invention.

It is therefore respectfully submitted that the prior art utilized by the Examiner fails to teach or suggest the method of independent claims 1 and 18, as well as their dependent claims. Accordingly, reconsideration and withdrawal of the 35 USC 102(e) rejections are respectfully requested.

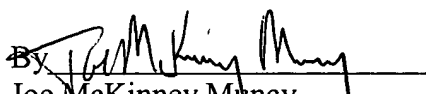
Favorable reconsideration and an early Notice of Allowance are earnestly solicited.

In the event that any outstanding matters remain in this application, the Examiner is invited to contact the undersigned at (703) 205-8000 in the Washington, D.C. area.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

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Respectfully submitted,


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